



CORNERSTONE Device Dimensions for 340 nm SOI Platform

Grating etch depth = 140 nm





Changes from previous version

Components added:

- 1550_TE 2x2 STRIP MMI
- 1310_TE grating coupler
- 1310_TE 1x2 STRIP MMI
- 1310_TE 2x2 STRIP MMI



TE mode
 $\lambda = 1550 \text{ nm}$

Grating etch depth = 140 nm

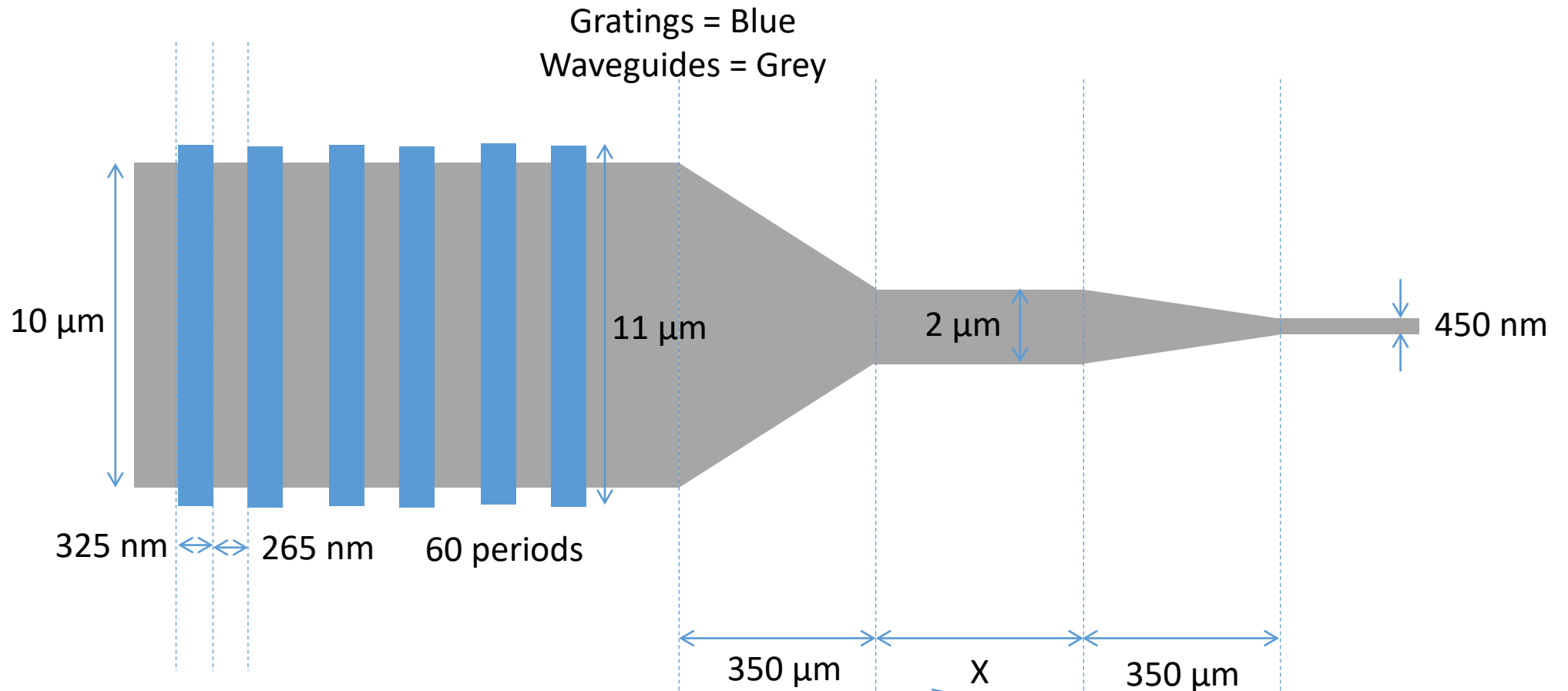




TE single mode waveguides and bends

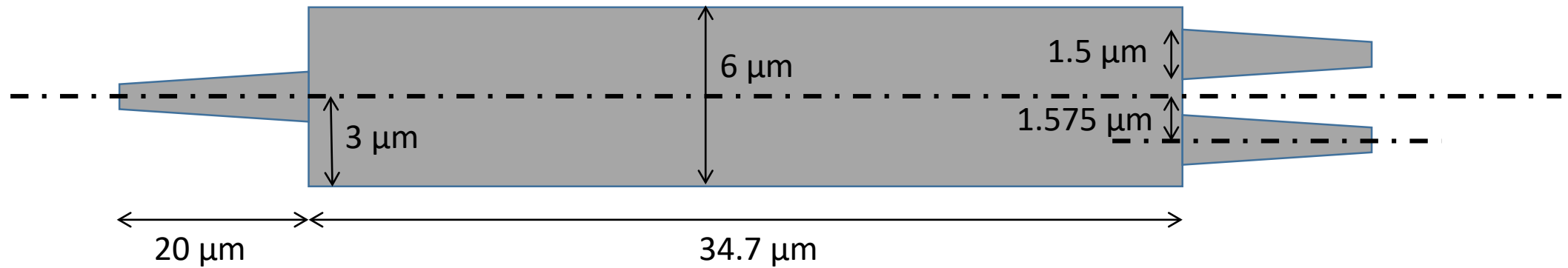
Property	Wavelength = 1550 nm
<u>Strip waveguides</u>	
Maximum single mode waveguide width (nm)	450
Minimum bend radius (width = 450 nm) (μm)	10

TE grating coupler (etch depth = 140 nm)



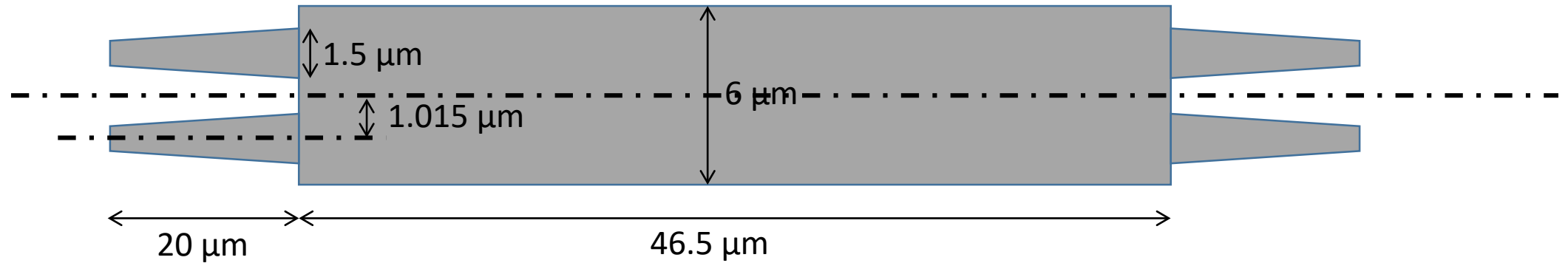
Use waveguide of width X for low loss routing to devices if required

TE 1x2 STRIP MMI dimensions



TE 2x2 MMI STRIP dimensions

Prototype device, not yet tested





TE mode
 $\lambda = 1310 \text{ nm}$

Grating etch depth = 140 nm



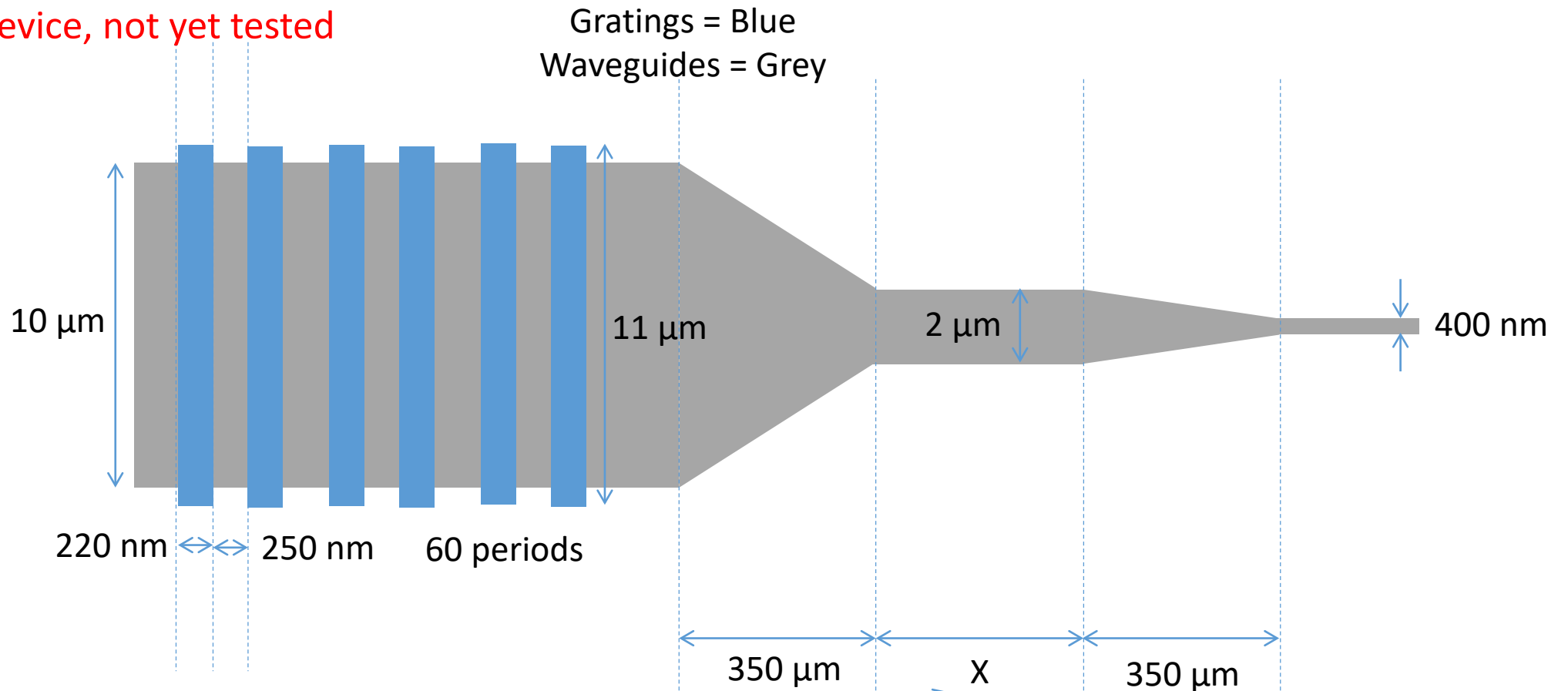


TE single mode waveguides and bends

Property	Wavelength = 1310 nm
<u>Strip waveguides</u>	
Maximum single mode waveguide width (nm)	400
Minimum bend radius (width = 400 nm) (μm)	10

TE grating coupler (etch depth = 140 nm)

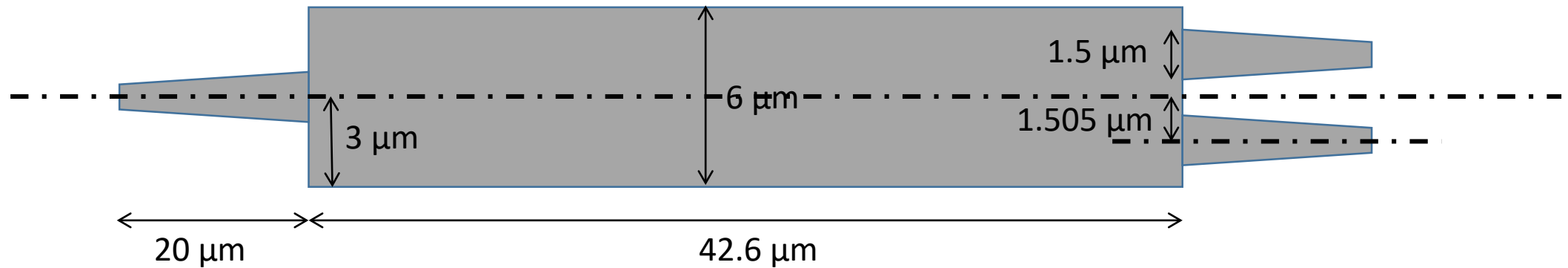
Prototype device, not yet tested



Use waveguide of width X for low loss routing to devices if required

TE 1x2 STRIP MMI dimensions

Prototype device, not yet tested



TE 2x2 STRIP MMI dimensions

Prototype device, not yet tested

